

Features

- Half-bridge SCR configuration integrated in a single package
- With high thermal conductivity DBC as the Insulation
- Welding by vacuum welding technology, which provide di7bT74747-99 0 Td928

Product Summary

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak off-state voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{DRM}	1600	V
Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1600	V
Non-repetitive peak off-state voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{DSM}	1700	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RSM}	1700	V
Average forward current	$T_{\text{C}} = 85^{\circ}\text{C}$	$I_{\text{T(AV)}}$	250	A
Forward surge current	$t_{\text{P}}=10\text{ms } V_{\text{R}}=0.6V_{\text{RRM}}$	I_{TSM}	8300	A
I^2t value for fusing		I^2t	344450	A^2s

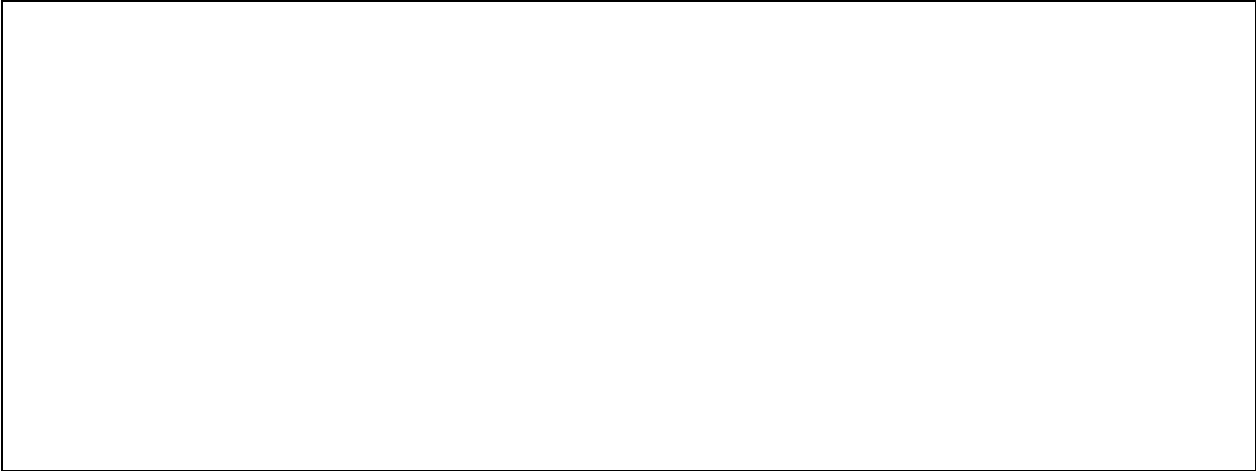
Critical rate of rise of on-state current I_{G}

Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

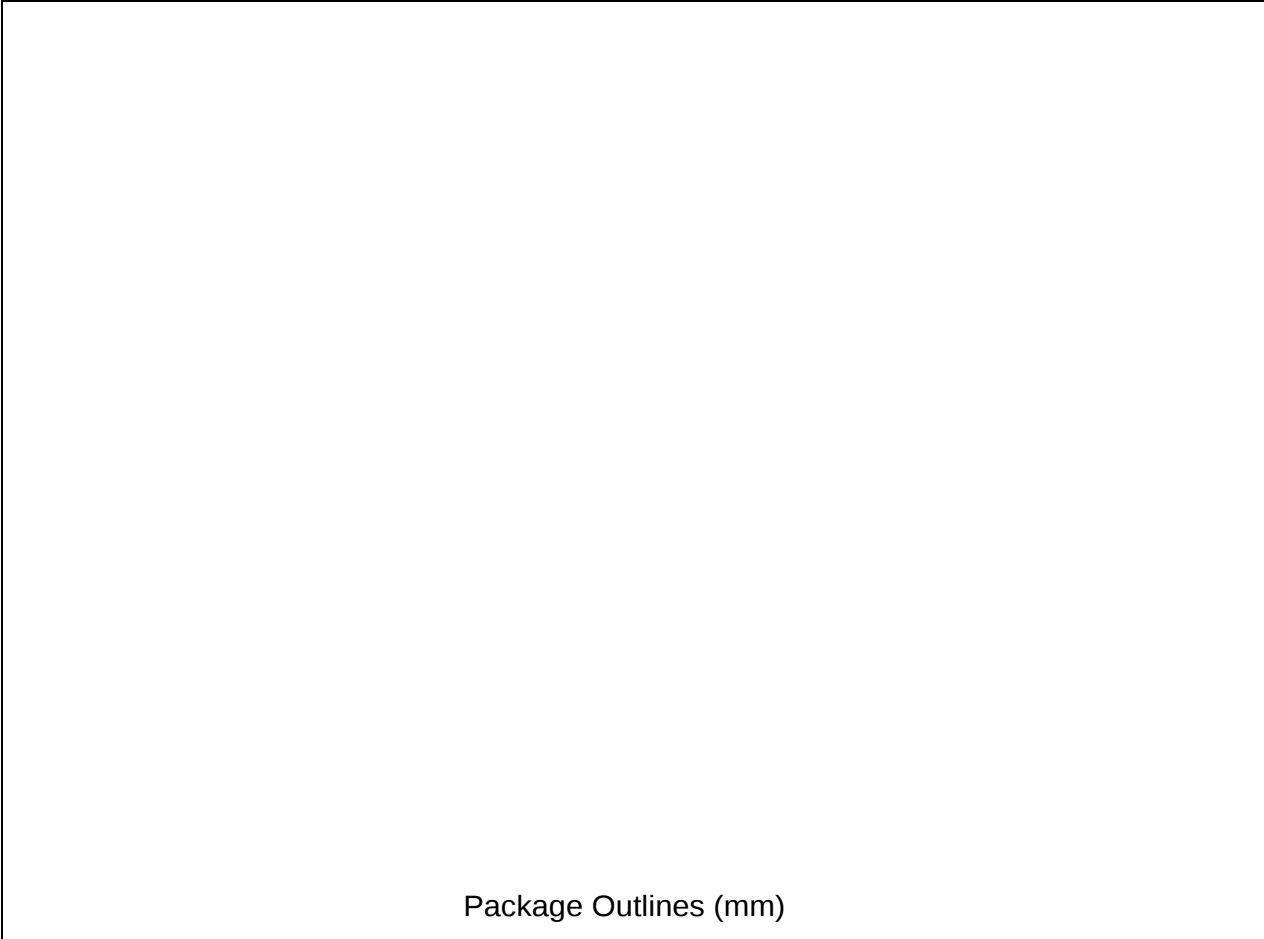
Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	

Peak forward voltage	I _T =750					
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Circuit Diagram



Package Outlines (mm)



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